



# HG15N135F1A

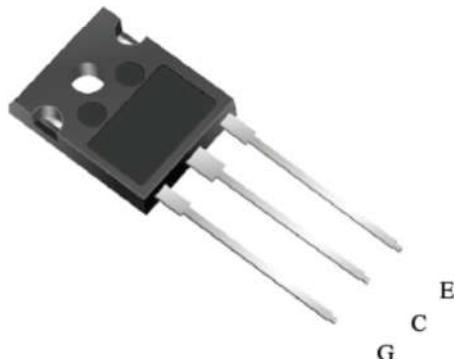
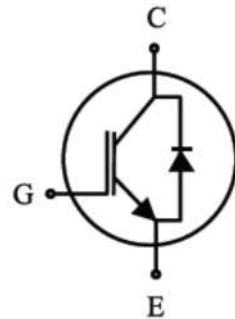
1350V/15A Trench Field Stop IGBT

Lu-semi Field Stop Trench IGBTs offer low switching losses, high energy efficiency and high avalanche ruggedness for soft switching applications such as inductive heating, microwave oven, etc.

V <sub>CE</sub>	1350	V
I <sub>C</sub>	15	A
V <sub>CE(SAT)</sub> I <sub>C</sub> =15A	1.9	V

## FEATURES

- Trench-Stop Technology offering :
  - High speed switching
  - High ruggedness, temperature stable
  - Low V<sub>CEsat</sub>
  - Easy parallel switching capability due to positive temperature coefficient in V<sub>CEsat</sub>
- Soft current turn-off waveforms
- Enhanced avalanche capability



## APPLICATION

- Inductive cooking
- Inverterized microwave ovens
- Resonant converters
- Soft switching applications



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### Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter Breakdown Voltage	$V_{CE}$	1350	V
DC collector current, limited by $T_{jmax}$ $T_C = 25^\circ C$ $T_C = 100^\circ C$	$I_C$	30 15	A
Diode Forward current, limited by $T_{jmax}$ $T_C = 25^\circ C$ $T_C = 100^\circ C$	$I_F$	30 15	A
Pulsed collector current, $t_p$ limited by $T_{jmax}$	$I_{Cpuls}$	45	A
Turn off safe operating area $V_{CE} \leq 1350V$ , $T_j \leq 150^\circ C$	-	45	A
Operating junction temperature $T_j$	-	-40...+150	°C
Storage temperature	$T_s$	-55...+150	°C
Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s	-	260	°C

### Thermal Resistance

Parameter	Symbol	Max. Value	Unit
IGBT thermal resistance, junction - case	$R_\theta(j-c)$	0.7	K/W
Diode thermal resistance, junction - case	$R_\theta(j-c)$	1.5	K/W
Thermal resistance, junction - ambient	$R_\theta(j-a)$	40	K/W



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**Electrical Characteristics of the IGBT** ( $T_j = 25^\circ\text{C}$  unless otherwise specified) :

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Collector-Emitter breakdown voltage	$\text{BV}_{\text{CES}}$	$\text{V}_{\text{GE}}=0\text{V}, \text{I}_C=250\mu\text{A}$ ①	1350	-	-	V
Gate threshold voltage	$\text{V}_{\text{GE}(\text{th})}$	$\text{V}_{\text{GE}}=\text{V}_{\text{CE}}, \text{I}_C=250\mu\text{A}$	5.1	5.8	6.4	V
Collector-Emitter Saturation voltage	$\text{V}_{\text{CE}(\text{sat})}$	$\text{V}_{\text{GE}}=15\text{V}, \text{I}_C=15\text{A}$ $T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	-	1.9 2.3	2.3 -	V
Zero gate voltage collector current	$\text{I}_{\text{CES}}$	$\text{V}_{\text{CE}} = 1350\text{V}, \text{V}_{\text{GE}} = 0\text{V}$ $T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	-	-	100 1000	$\mu\text{A}$
Gate-emitter leakage current	$\text{I}_{\text{GES}}$	$\text{V}_{\text{CE}} = 0\text{V}, \text{V}_{\text{GE}} = 20\text{V}$	-	-	100	nA

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>Dynamic</b>						
Input capacitance	$\text{C}_{\text{ies}}$		-	1655	-	pF
Output capacitance	$\text{C}_{\text{oes}}$	$\text{V}_{\text{CE}} = 25\text{V}, \text{V}_{\text{GE}} = 0\text{V},$ $f = 1\text{MHz}$	-	72	-	
Reverse transfer capacitance	$\text{C}_{\text{res}}$		-	35	-	
Gate charge	$\text{Q}_G$	$\text{V}_{\text{CC}} = 600\text{V}, \text{I}_C = 15\text{A},$ $\text{V}_{\text{GE}} = 15\text{V}$	-	101	-	nC

### Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>Dynamic , at <math>T_j = 25^\circ\text{C}</math></b>						
Turn-off delay time	$\text{t}_{\text{d}(\text{off})}$		-	80	-	ns
Fall time	$\text{t}_f$	$\text{V}_{\text{CC}} = 600\text{V}, \text{I}_C = 15\text{A},$ $\text{V}_{\text{GE}} = 0/15\text{V},$ $R_g = 12\Omega$	-	200	-	ns
Turn-off energy	$\text{E}_{\text{off}}$		-	0.28	-	mJ

Note:

①  $\text{BV}_{\text{ces}}$  testing without filter could damage the device.  $\text{BV}_{\text{ces}}$  is guaranteed by  $\text{I}_{\text{ces}}@1350\text{V}$  test.



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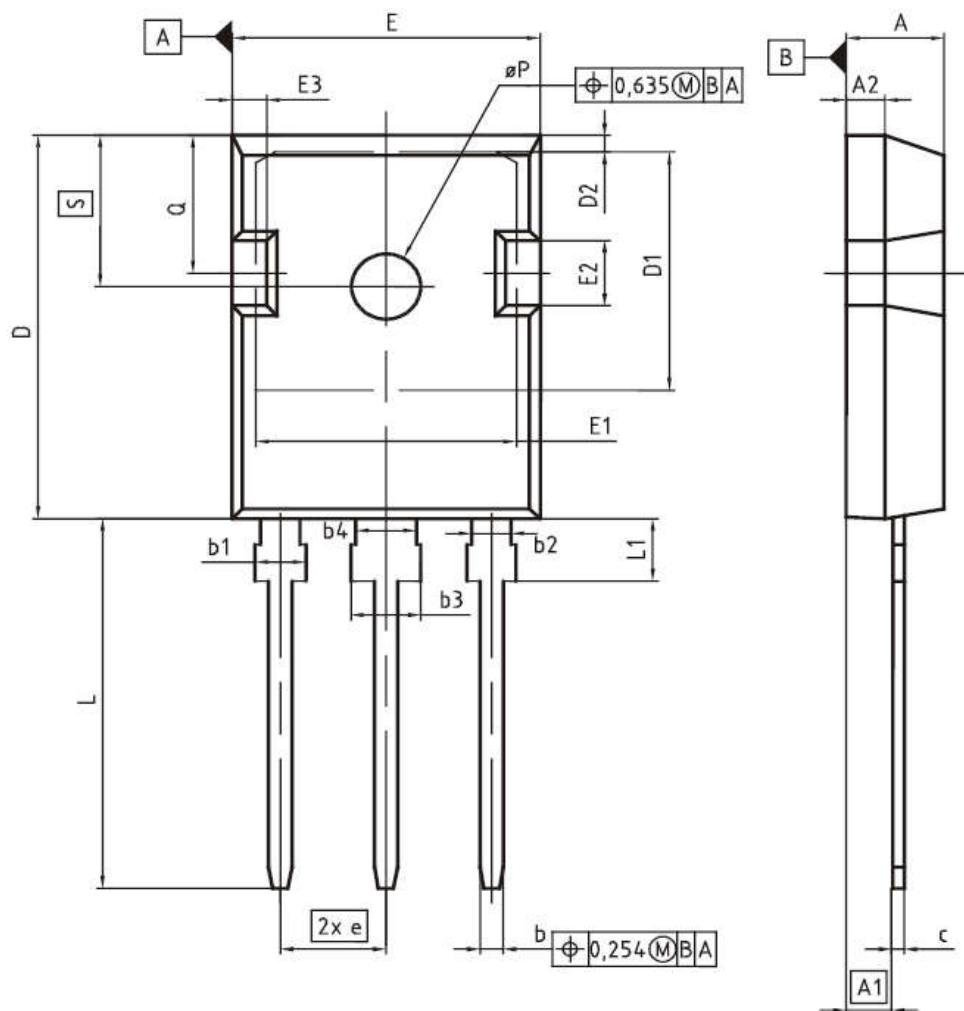
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**Electrical Characteristics of the DIODE** ( $T_j = 25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>Dynamic</b>						
Diode Forward Voltage	$V_{FM}$	$I_F = 15\text{A}$	-	2.3	-	V
Reverse Recovery Time	$T_{rr}$	$I_F = 10\text{A},$ $di/dt = 200\text{A}/\mu\text{s}$	-	70	-	ns
Reverse Recovery Current	$I_{rr}$		-	5	-	A
Reverse Recovery Charge	$Q_{rr}$		-	1600	-	nC

**PG-T0247-3**



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44 (BSC)		0.214 (BSC)	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
$\phi P$	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248